

isc Silicon NPN Power Transistor

3DD200

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min.})$
- DC Current Gain-
: $h_{FE} = 30 \sim 120(\text{Min.}) @ I_C = 2A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 1.5V(\text{Max}) @ I_C = 3A$

APPLICATIONS

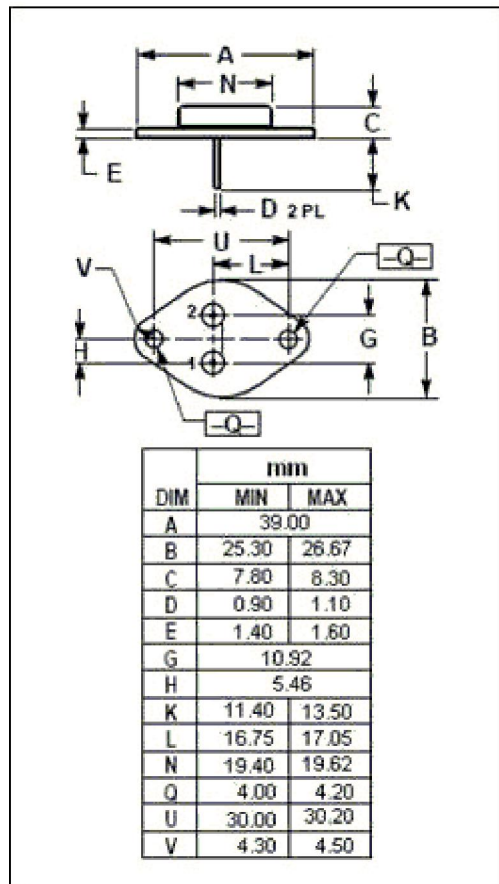
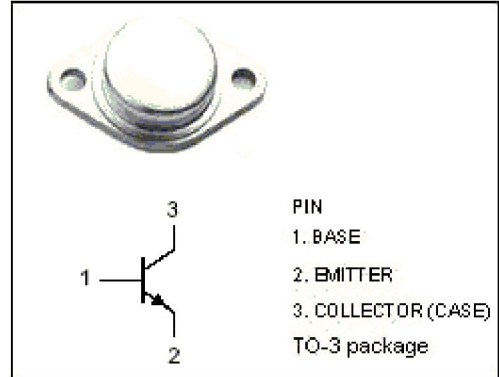
- Designed for B&W TV horizontal output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	3	A
P_C	Collector Power Dissipation@ $T_C=75^\circ C$	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.5	$^\circ C/W$



isc Silicon NPN Power Transistors**3DD200****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	100		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	250		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=150\text{V}; I_E=0$		0.5	mA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=5\text{V}$	30	120	
t_f	Fall Time	$I_C=3\text{A}; I_{B1}=0.2\text{A}, I_{B2}=-0.3\text{A}$		1.0	μs